

# 2SA2084

Silicon PNP epitaxial planar type

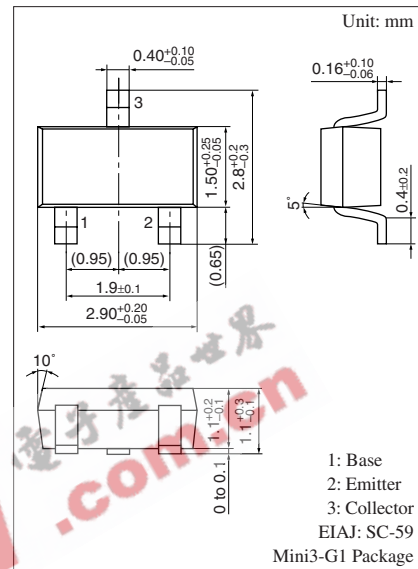
For general amplification

## ■ Features

- High collector-emitter voltage (Base open)  $V_{CEO}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-300	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-300	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-70	mA
Peak collector current	$I_{CP}$	-100	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 7N

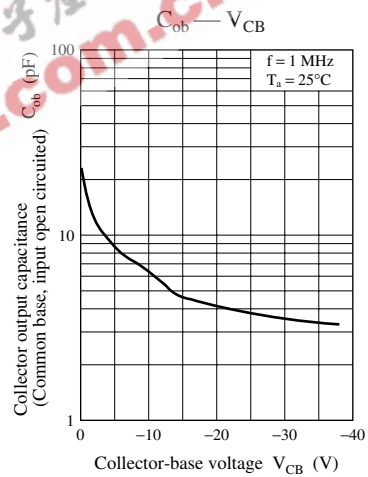
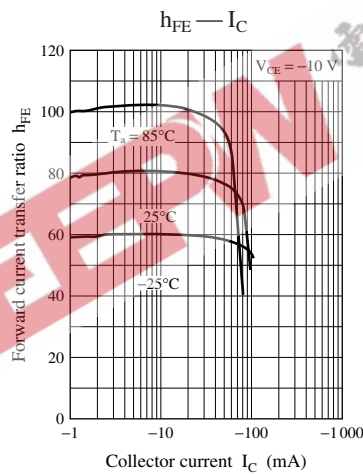
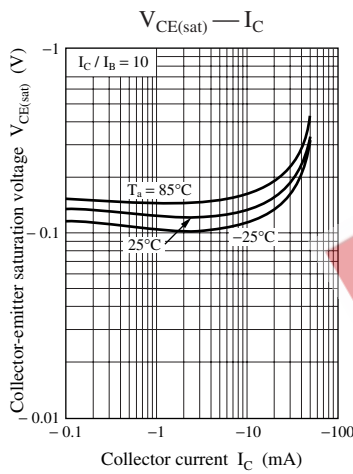
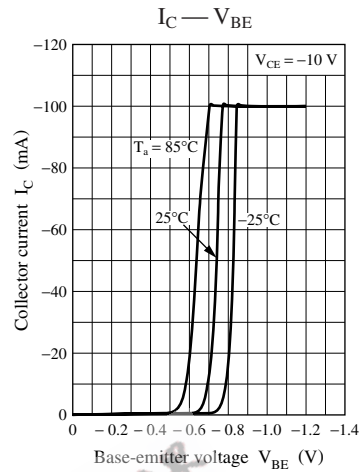
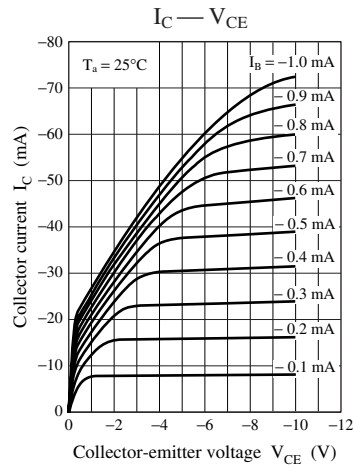
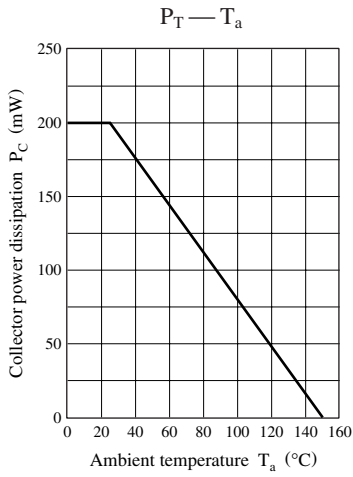
## ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -100 \mu\text{A}, I_B = 0$	-300			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -1 \mu\text{A}, I_C = 0$	-5			V
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	30		150	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-0.6	V
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		7		pF
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$		50		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	P	Q
$h_{FE}$	30 to 100	60 to 150



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